

UTC UNISONIC TECHNOLOGIES CO., LTD

60N06

Power MOSFET

60A, 60V N-CHANNEL **POWER MOSFET**

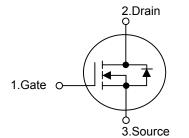
DESCRIPTION

The UTC 60N06 is N-channel enhancement mode power field effect transistors with stable off-state characteristics, fast switching speed, low thermal resistance, usually used at telecom and computer application.

FEATURES

- * $R_{DS(ON)}$ = 18m Ω @V_{GS} = 10 V
- * Ultra low gate charge (typical 39nC)
- * Fast switching capability
- * Low reverse transfer Capacitance (C_{\text{RSS}}= typical 115pF)
- * Avalanche energy Specified
- * Improved dv/dt capability, high ruggedness

SYMBOL

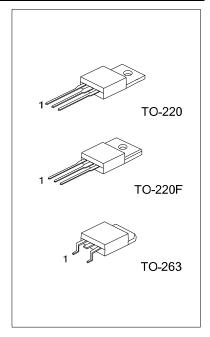


ORDERING INFORMATION

Ordering Number		Deekeese	Pin Assignment			Decking	
Lead Free	Halogen Free	Package	1	2	3	Packing	
60N06L-TA3-T	60N06G-TA3-T	TO-220	G	D	S	Tube	
60N06L-TF3-T	60N06G-TF3-T	TO-220F	G	D	S	Tube	
60N06L-TQ2-R	60N06G-TQ2-R	TO-263	G	D	S	Tape Reel	
60N06L-TQ2-T	60N06G-TQ2-T	TO-263	G	D	S	Tube	

Note: Pin Assignment: G: Gate D: Drain S: Source

60N06 <u>L-TA3-T</u>	(1) Packing Type (2) Package Type (3) Lead Free	(1) T: Tube (2) TA3: TO-220, TF3: TO-220F, TQ2: TO-263 (3) G: Halogen Free, L: Lead Free
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■ ABSOLUTE MAXIMUM RATINGS

PARAMETER		SYMBOL	RATINGS	UNIT
Drain to Source Voltage		V _{DSS}	60	V
Gate to Source Voltage		V_{GS}	±20	V
Continuous Drain Current	T _C = 25°C		60	А
	T _C = 100°C	Ι _D	39	А
Drain Current Pulsed (Note 2)		I _{DM}	120	А
Austausha Eusees	Single Pulsed (Note 3)	E _{AS}	1000	mJ
Avalanche Energy	Repetitive (Note 2)	E _{AR}	180	mJ
	TO-220		100	
Power Dissipation	TO-220F	PD	70.62	W
(T _C =25°C)	TO-263		54	
Junction Temperature	on Temperature T		+150	°C
Storage Temperature		T _{STG}	-55 ~ +150	°C

Note: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.

- 2. Repeativity rating: pulse width limited by junction temperature
- 3. L=0.61mH, I_{AS}=60A, R_G=20\Omega, Starting T_J=25 $^\circ\!\mathrm{C}$

THERMAL DATA

PARAMETER		SYMBOL	RATINGS	UNIT
Junction to Ambient	TO-220/TO-220F	0	62.5	°C 14/
	TO-263	θ_{JA}	110	°C/W
Junction to Case	TO-220		1.25	
	TO-220F	θ _{JC}	1.77	°C/W
	TO-263		2.31	

ELECTRICAL CHARACTERISTICS (T_c = 25°C, unless otherwise specified)

PARAMETER		SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
OFF CHARACTERISTICS							
Drain-Source Breakdown Voltage		BV _{DSS}	V _{GS} = 0 V, I _D = 250µA	60			V
Drain-Source Leakage Current		I _{DSS}	V _{DS} = 60 V, V _{GS} = 0 V			1	μA
Cata Source Leakage Current	Forward	- I _{GSS}	V _{GS} = 20V, V _{DS} = 0 V			100	nA
Gate-Source Leakage Current	Reverse		V_{GS} = -20V, V_{DS} = 0 V			-100	nA
ON CHARACTERISTICS							
Gate Threshold Voltage		V _{GS(TH)}	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	2.0		4.0	V
Static Drain-Source On-State Resistance		R _{DS(ON)}	V _{GS} = 10 V, I _D = 30A		14	18	mΩ
DYNAMIC CHARACTERISTIC	S						
Input Capacitance		C _{ISS}			2000		pF
Output Capacitance		C _{OSS}	V _{GS} = 0V, V _{DS} =25V, f = 1MHz		400		рF
Reverse Transfer Capacitance		C _{RSS}			115		рF
SWITCHING CHARACTERIST	ICS						
Turn-On Delay Time		t _{D(ON)}			12	30	ns
Rise Time		t _R	V _{DD} =30V, I _D =60A, R _L =0.5Ω,		11	30	ns
Turn-Off Delay Time		t _{D(OFF)}	V _{GS} =10V (Note 2, 3)		25	50	ns
Fall Time		t _F			15	30	ns
Total Gate Charge	Total Gate Charge				39	60	nC
Gate-Source Charge		Q_{GS}	$V_{DS} = 30V, V_{GS} = 10V$		12		nC
Gate-Drain Charge (Miller Charge)		Q_{GD}	I _D = 60A (Note 2, 3)		10		nC



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■ ELECTRICAL CHARACTERISTICS(Cont.)

PARAMETER	SYMBOL	TEST CONDITIONS		TYP	MAX	UNIT		
SOURCE-DRAIN DIODE RATINGS AND CHARACTERISTICS								
Diode Forward Voltage	V _{SD}	V _{GS} = 0 V, I _S = 60A			1.6	V		
Continuous Source Current	ls				60	•		
Pulsed Source Current	I _{SM}				120	A		
Reverse Recovery Time	t _{rr}	−I _S =60A, V _{GS} =0V, dI _F /dt=100A/µs		60		ns		
Reverse Recovery Charge	Q _{RR}			3.4		μC		

Note: 1. I_{SD}≤60A, di/dt≤300A/ μ s, V_{DD}≤BV_{DSS}, Starting T_J=25°C

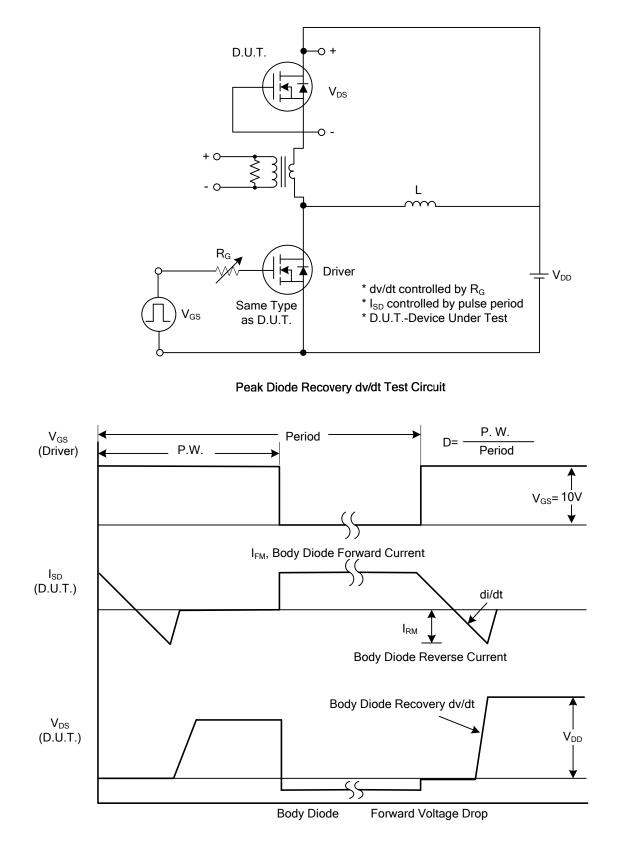
2. Pulse Test: Pulse Width≤300µs, Duty Cycle≤2%

3. Essentially independent of operating temperature.



■ TEST CIRCUITS AND WAVEFORMS

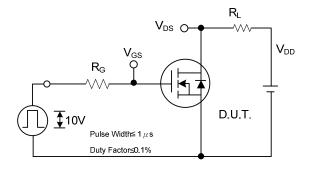
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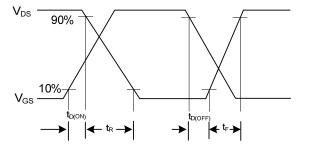
Peak Diode Recovery dv/dt Waveforms



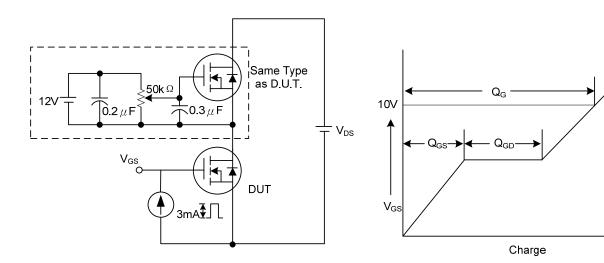
■ TEST CIRCUITS AND WAVEFORMS (Cont.)



Switching Test Circuit

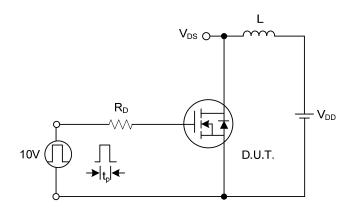


Switching Waveforms



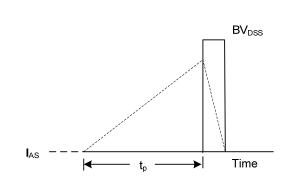
Gate Charge Test Circuit

Gate Charge Waveform



Unclamped Inductive Switching Test Circuit

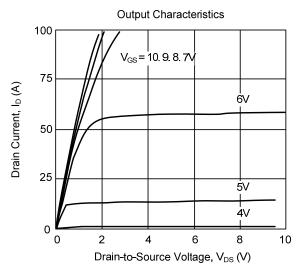


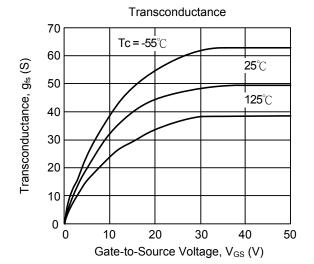


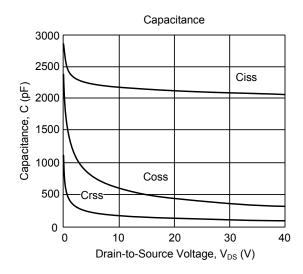
Unclamped Inductive Switching Waveforms

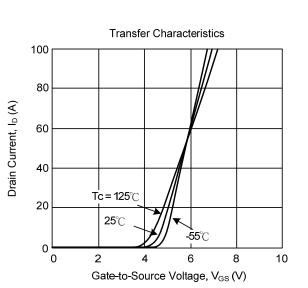
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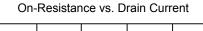
TYPICAL CHARACTERISTICS

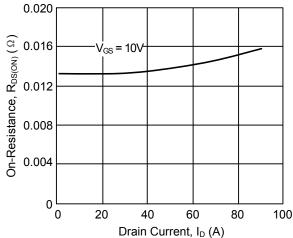


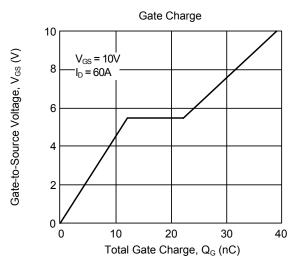






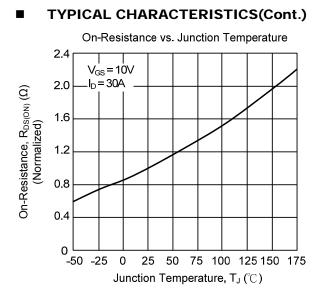


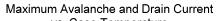


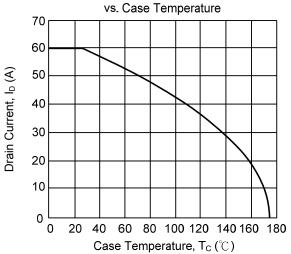




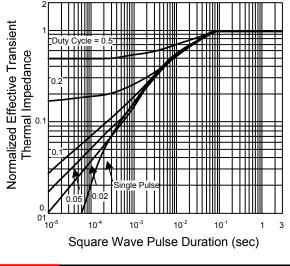
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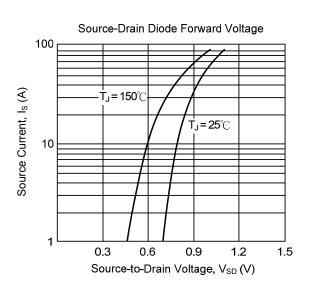


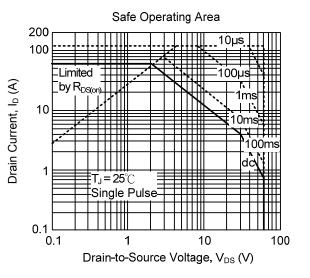
Normalized Thermal Transient Impedance





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